

IRHMS67260 (JANSR2N7584T1)

PD-94667J

Radiation Hardened Power MOSFET Thru-Hole (Low Ohmic TO-254AA) 200V, 45A, N-channel, R6 Technology

Features

- Single event effect (SEE) hardened (up to LET of 90 MeV·cm²/mg)
- Low R_{DS(on)}
- Fast switching
- Low total gate charge
- Simple drive requirements
- Hermetically sealed
- Electrically isolated
- Ceramic eyelets
- Light weight
- ESD rating: Class 3A per MIL-STD-750, Method 1020

Potential Applications

- DC-DC converter
- Motor drives
- Electric propulsion

Product Validation

Qualified to JANS screening flow according to MIL-PRF-19500 for space applications

Description

IR HiRel IR HiRel R6 technology provides high performance power MOSFETs for space applications. These devices have been characterized for both Total Dose and Single Event Effect (SEE) with useful performance up to LET of 90 MeV·cm²/mg. The combination of low R_{DS(on)} and low gate charge reduces the power losses in switching applications such as DC-DC converters and motor controllers. These devices retain all of the well-established advantages of MOSFETs such as voltage control, fast switching and temperature stability of electrical parameters.

Ordering Information

Table 1 Ordering options

Part number	Package	Screening Level	TID Level
IRHMS67260	Low-Ohmic TO-254AA	COTS	100 krad (Si)
JANSR2N7584T1	Low-Ohmic TO-254AA	JANS	100 krad (Si)
IRHMS63260	Low-Ohmic TO-254AA	COTS	300 krad (Si)
JANSF2N7584T1	Low-Ohmic TO-254AA	JANS	300 krad (Si)

Product Summary

- **BV_{DSS}**: 200V
- **I_D**: 45A
- **R_{DS(on),max}**: 29mΩ
- **Q_{Gmax}**: 240nC
- **REF**: MIL-PRF-19500/753



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Absolute Maximum Ratings

1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings (Pre-Irradiation)

Symbol	Parameter	Value	Unit
I_{D1} @ $V_{GS} = 12V$, $T_C = 25^\circ C$	Continuous Drain Current	45*	A
I_{D2} @ $V_{GS} = 12V$, $T_C = 100^\circ C$	Continuous Drain Current	35	A
I_{DM} @ $T_C = 25^\circ C$	Pulsed Drain Current ¹	180	A
P_D @ $T_C = 25^\circ C$	Maximum Power Dissipation	208	W
	Linear Derating Factor	1.67	W/ $^\circ C$
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ²	344	mJ
I_{AR}	Avalanche Current ¹	45	A
E_{AR}	Repetitive Avalanche Energy ¹	20.8	mJ
dv/dt	Peak Diode Reverse Recovery ³	5.4	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	9.3 (Typical)	

*Current is limited by package

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.² $V_{DD} = 25V$, starting $T_J = 25^\circ C$, $L = 0.34mH$, Peak $I_L = 45A$, $V_{GS} = 12V$ ³ $I_{SD} \leq 45A$, $di/dt \leq 840A/\mu s$, $V_{DD} \leq 200V$, $T_J \leq 150^\circ C$

Device Characteristics
2 Device Characteristics
2.1 Electrical Characteristics (Pre-Irradiation)
Table 3 Static and Dynamic Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 1.0mA$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.21	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1.0mA$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	29	m Ω	$V_{GS} = 12V, I_{D2} = 35A^1$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 1mA$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-11.2	—	mV/ $^\circ\text{C}$	
G_{fs}	Forward Transconductance	40	—	—	S	$V_{DS} = 15V, I_{D2} = 35A^1$
I_{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	$V_{DS} = 160V, V_{GS} = 0V$
		—	—	25		$V_{DS} = 160V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Leakage Reverse	—	—	-100		$V_{GS} = -20V$
Q_G	Total Gate Charge	—	—	240	nC	$I_{D1} = 45A$
Q_{GS}	Gate-to-Source Charge	—	—	65		$V_{DS} = 100V$
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	60		$V_{GS} = 12V$
$t_{d(on)}$	Turn-On Delay Time	—	—	40	ns	$I_{D1} = 45A^{**}$ $V_{DD} = 100V$ $R_G = 2.35\Omega$ $V_{GS} = 12V$
t_r	Rise Time	—	—	125		
$t_{d(off)}$	Turn-Off Delay Time	—	—	85		
t_f	Fall Time	—	—	30		
$L_s + L_D$	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm / 0.25in from package) to Source lead (6mm / 0.25in from package) with Source wire internally bonded from Source pin to Drain pad
C_{iss}	Input Capacitance	—	8045	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	953	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	14	—		$f = 100KHz$
R_G	Gate Resistance	—	1.1	—	Ω	$f = 1.0MHz$, open drain

****** Switching speed maximum limits are based on manufacturing test equipment and capability.

¹ Pulse width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2\%$

Device Characteristics

2.2 Source-Drain Diode Ratings and Characteristics (Pre-Irradiation)

Table 4 Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	45	A	
I_{SM}	Pulsed Source Current (Body Diode) ¹	—	—	180	A	
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}$, $I_S = 45\text{A}$, $V_{GS} = 0\text{V}$ ²
t_{rr}	Reverse Recovery Time	—	—	640	ns	$T_J = 25^\circ\text{C}$, $I_F = 45\text{A}$, $V_{DD} \leq 25\text{V}$ $di/dt = 100\text{A}/\mu\text{s}$ ⁶
Q_{rr}	Reverse Recovery Charge	—	—	10.5	μC	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

2.3 Thermal Characteristics

Table 5 Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-Case	—	—	0.6	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Junction-to-Sink	—	0.21	—	
$R_{\theta JA}$	Junction-to-Ambient (Typical socket mount)	—	—	48	

2.4 Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 3 and 4) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

2.4.1 Electrical Characteristics — Post Total Dose Irradiation

Table 6 Electrical Characteristics @ $T_J = 25^\circ\text{C}$, Post Total Dose Irradiation^{3, 4}

Symbol	Parameter	Up to 300 krad (Si) ⁵		Unit	Test Conditions
		Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	—	V	$V_{GS} = 0\text{V}$, $I_D = 1.0\text{mA}$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0	V	$V_{DS} = V_{GS}$, $I_D = 1.0\text{mA}$
I_{GSS}	Gate-to-Source Leakage Forward	—	100	nA	$V_{GS} = 20\text{V}$
	Gate-to-Source Leakage Reverse	—	-100		$V_{GS} = -20\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	—	10	μA	$V_{DS} = 160\text{V}$, $V_{GS} = 0\text{V}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (TO-3) ²	—	29	$\text{m}\Omega$	$V_{GS} = 12\text{V}$, $I_{D2} = 35\text{A}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (Low- Ohmic TO-254AA) ²	—	29	$\text{m}\Omega$	$V_{GS} = 12\text{V}$, $I_{D2} = 35\text{A}$
V_{SD}	Diode Forward Voltage	—	1.2	V	$V_{GS} = 0\text{V}$, $I_F = 45\text{A}$

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.

² Pulse width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2\%$

³ Total Dose Irradiation with V_{GS} Bias. $V_{GS} = 12\text{V}$ applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁴ Total Dose Irradiation with V_{DS} Bias. $V_{DS} = 160\text{V}$ applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁵ Part numbers IRHMS67260 (JANSR2N7584T1) and IRHMS63260 (JANSR2F7584T1)

Device Characteristics

2.4.2 Single Event Effects — Safe Operating Area

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. 1 and Table 7.

Table 7 Typical Single Event Effects Safe Operating Area

LET (MeV·cm ² /mg)	Energy (MeV)	Range (μm)	V _{DS} (V)				
			V _{GS} = 0V	V _{GS} = -4V	V _{GS} = -5V	V _{GS} = -10V	V _{GS} = -15V
42 ± 5%	2450 ± 5%	205 ± 5%	200	200	200	200	190
61 ± 5%	825 ± 5%	66 ± 7.5%	200	200	200	200	190
90 ± 5%	1470 ± 5%	80 ± 5%	150	150	110	—	—

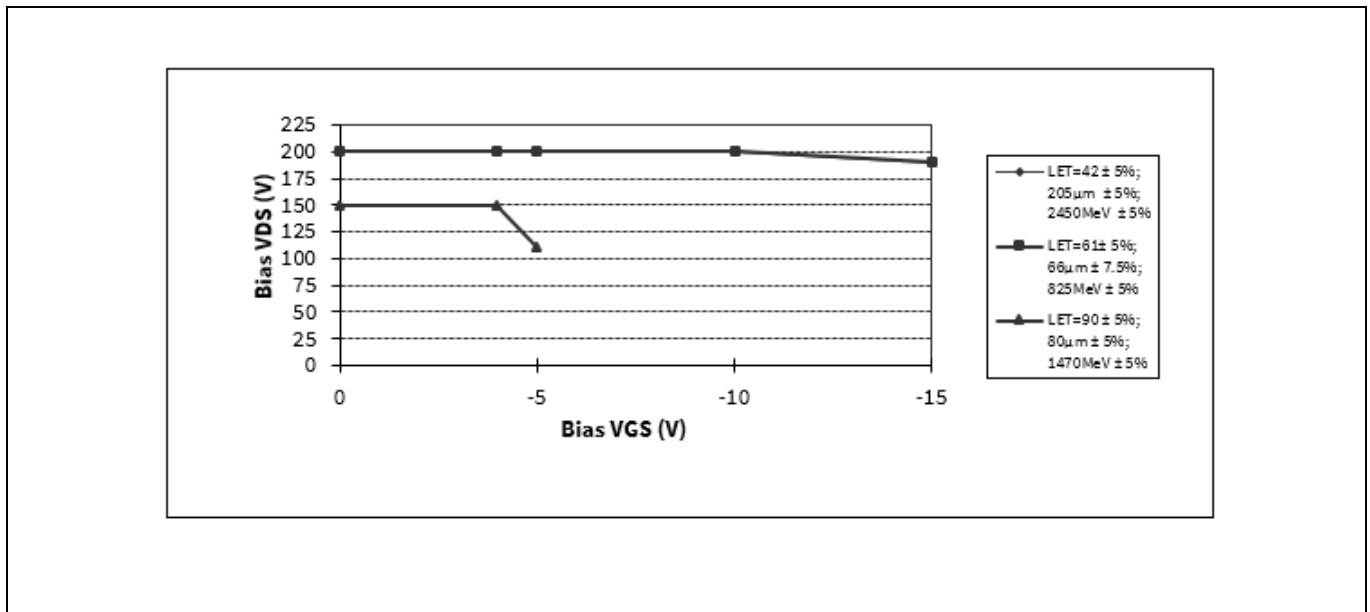


Figure 1 Typical Single Event Effect, Safe Operating Area

IRHMS67260 (JANSR2N7584T1)

Radiation Hardened Power MOSFET Thru-Hole (Low Ohmic TO-254AA)

Electrical Characteristics Curves (Pre-irradiation)

3 Electrical Characteristics Curves (Pre-irradiation)

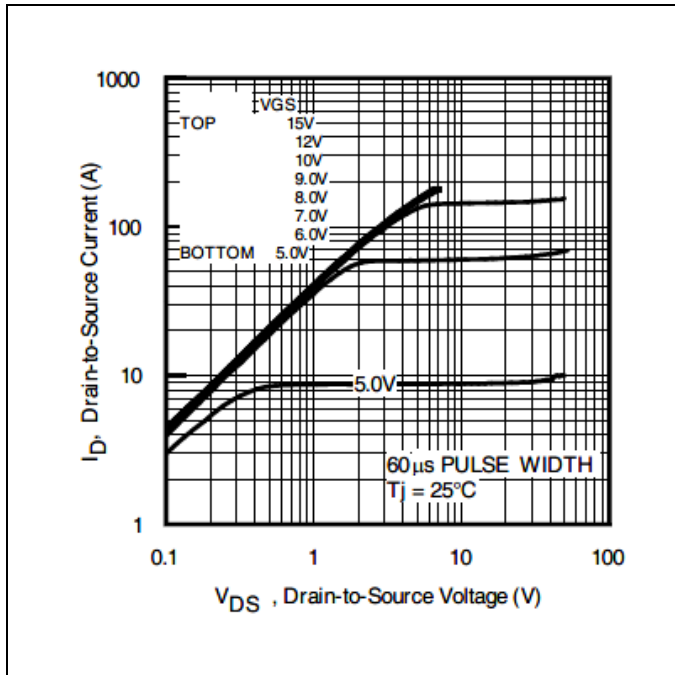


Figure 2 Typical Output Characteristics

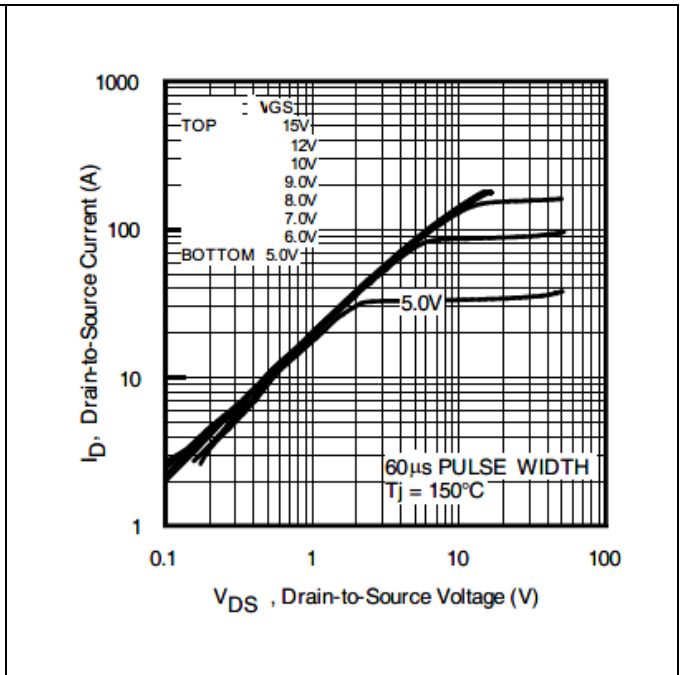


Figure 3 Typical Output Characteristics

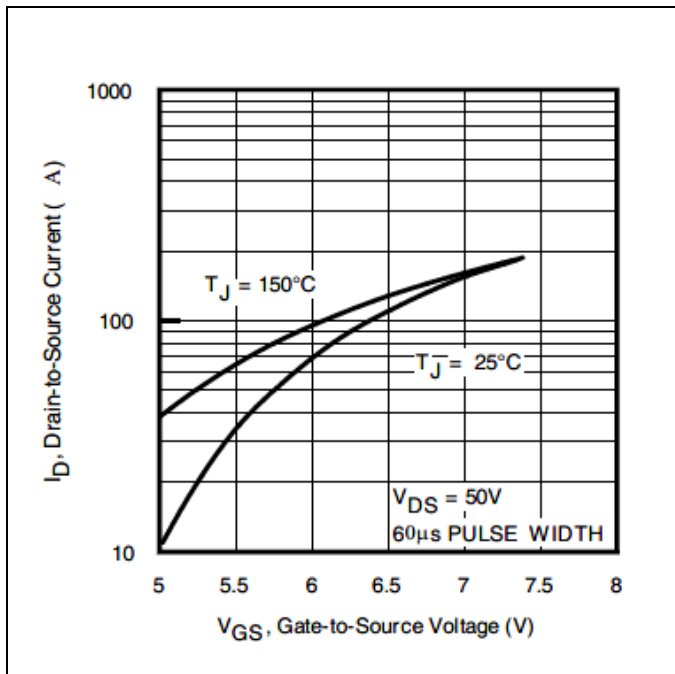


Figure 4 Typical Transfer Characteristics

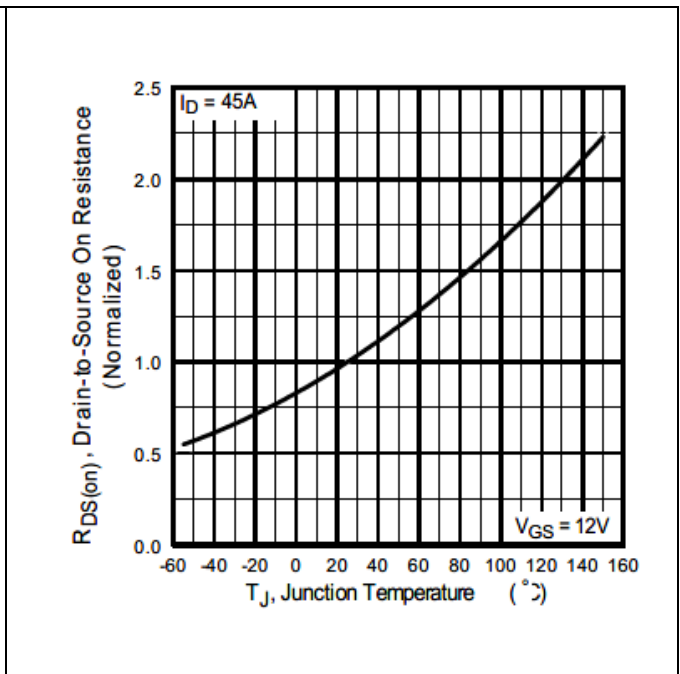


Figure 5 Normalized On-Resistance Vs. Temperature

IRHMS67260 (JANSR2N7584T1)

Radiation Hardened Power MOSFET Thru-Hole (Low Ohmic TO-254AA)

Electrical Characteristics Curves (Pre-irradiation)

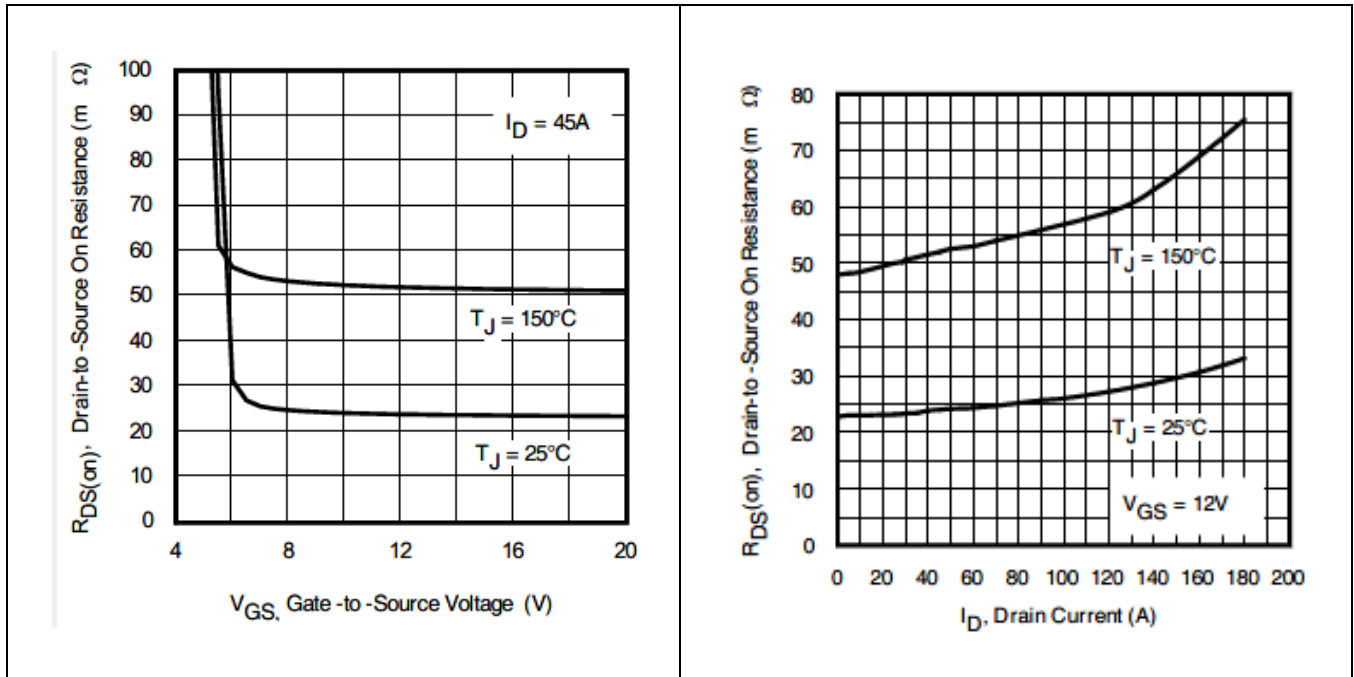


Figure 6 Typical On-Resistance Vs Gate Voltage

Figure 7 Typical On-Resistance Vs Drain Current

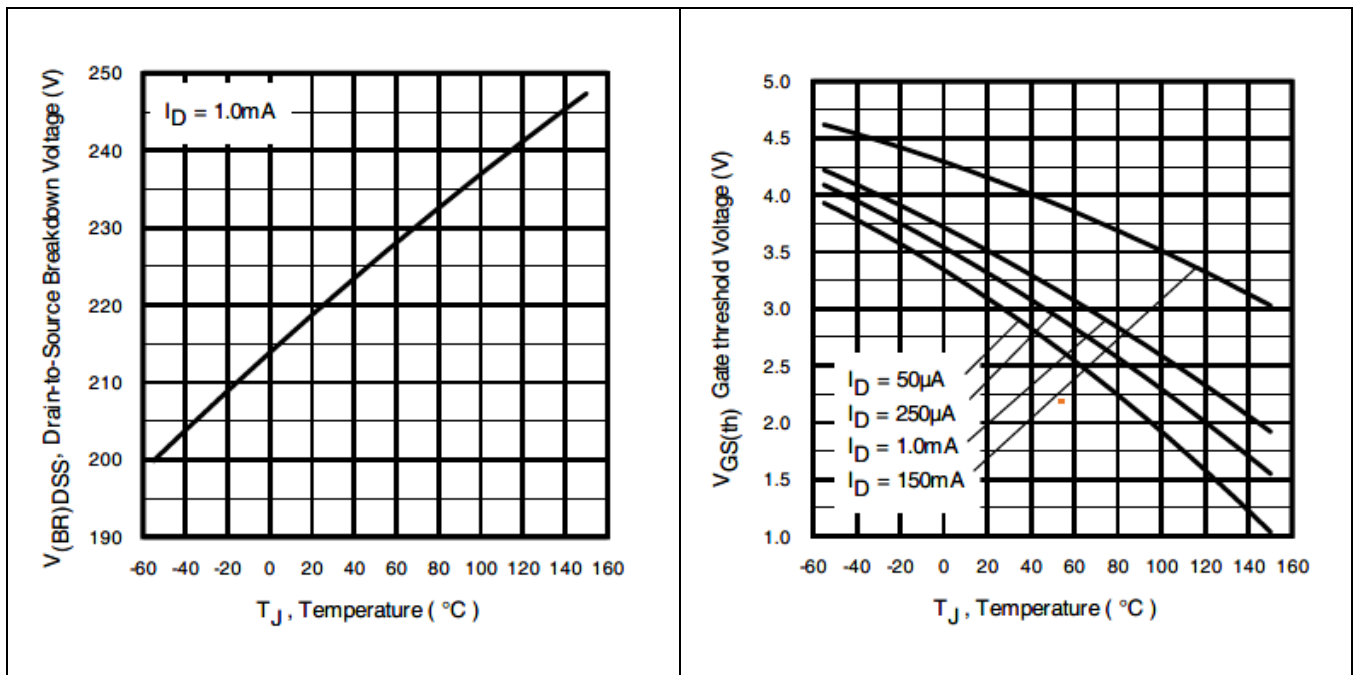


Figure 8 Typical Drain-to-Source Breakdown Voltage Vs. Temperature

Figure 9 Typical Threshold Voltage Vs. Temperature

IRHMS67260 (JANSR2N7584T1)

Radiation Hardened Power MOSFET Thru-Hole (Low Ohmic TO-254AA)

Electrical Characteristics Curves (Pre-irradiation)

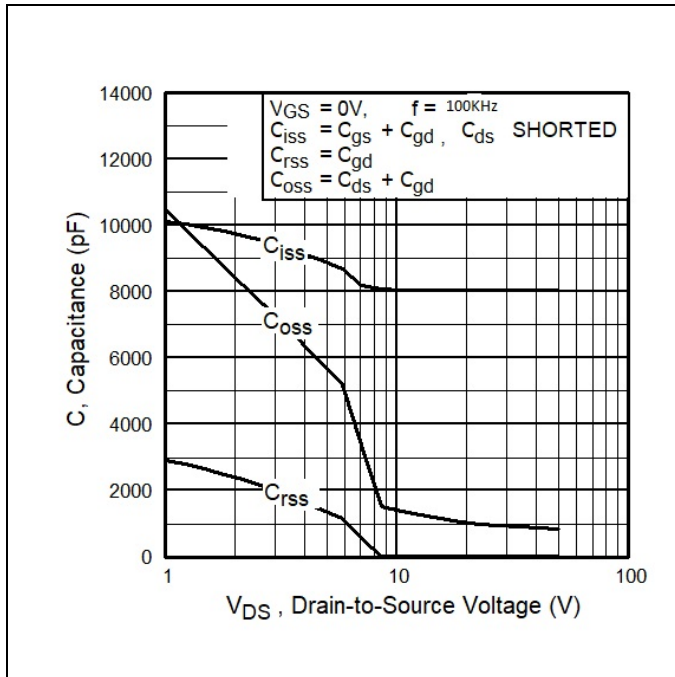


Figure 10 Typical Capacitance Vs. Drain-to-Source Voltage

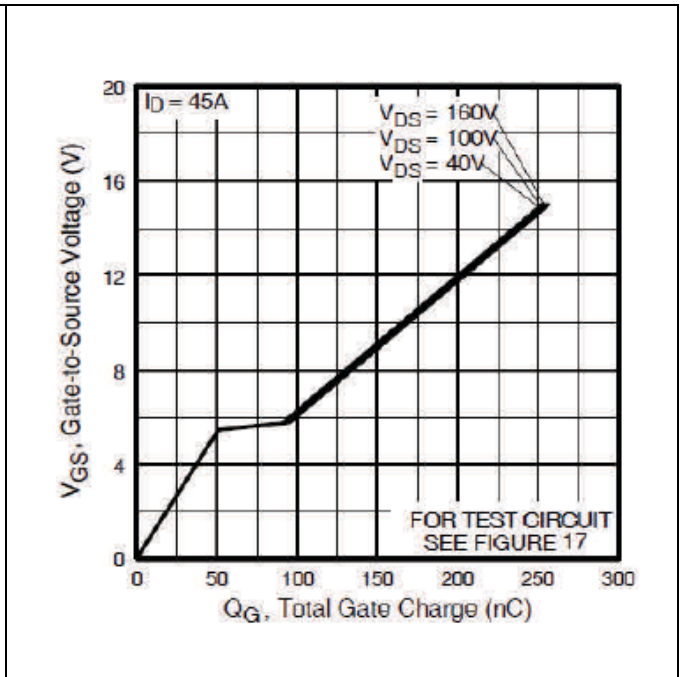


Figure 11 Gate-to-Source Voltage Vs. Typical Gate Charge

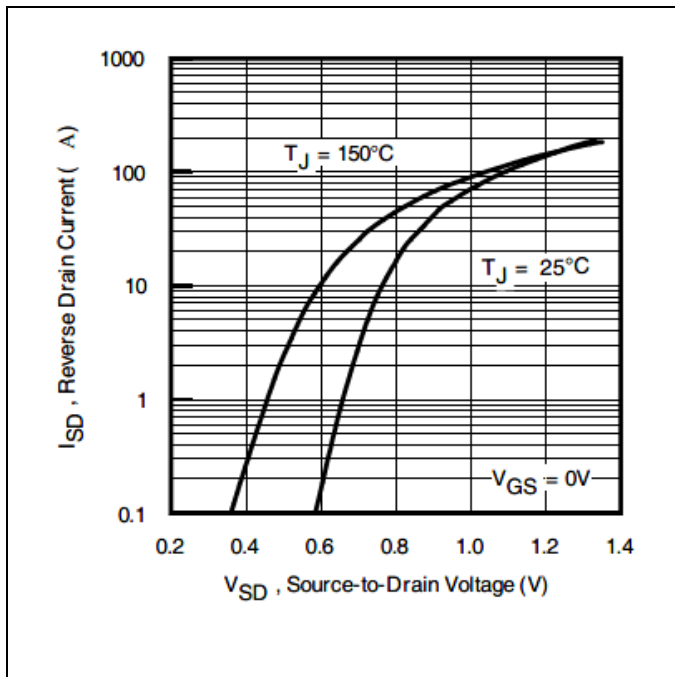


Figure 12 Typical Source-Drain Current Vs. Diode Forward Voltage

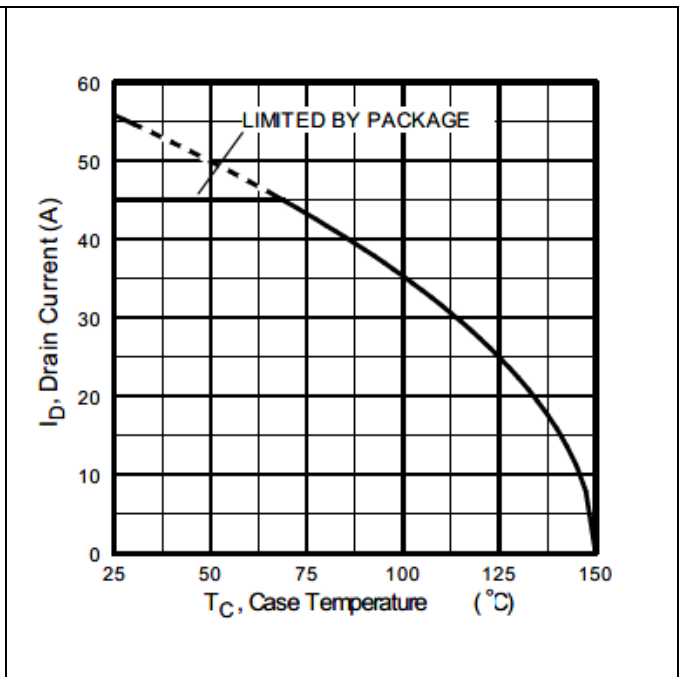


Figure 13 Maximum Drain Current Vs. Temperature

IRHMS67260 (JANSR2N7584T1)

Radiation Hardened Power MOSFET Thru-Hole (Low Ohmic TO-254AA)

Electrical Characteristics Curves (Pre-irradiation)

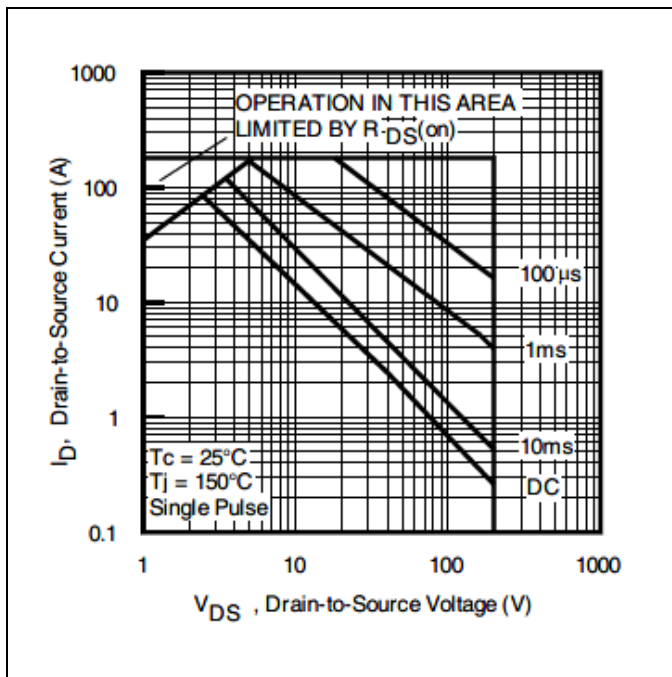


Figure 14 Maximum Safe Operating Area

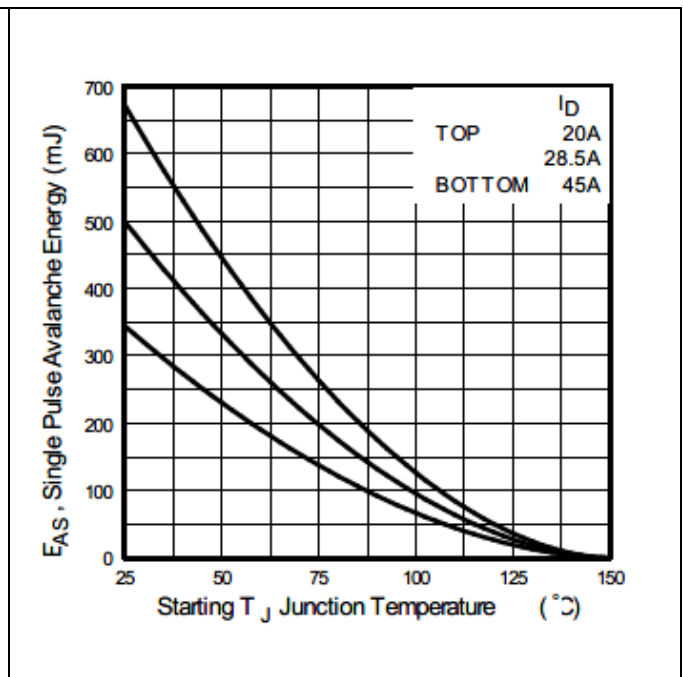


Figure 15 Maximum Avalanche Energy Vs. Junction Temperature

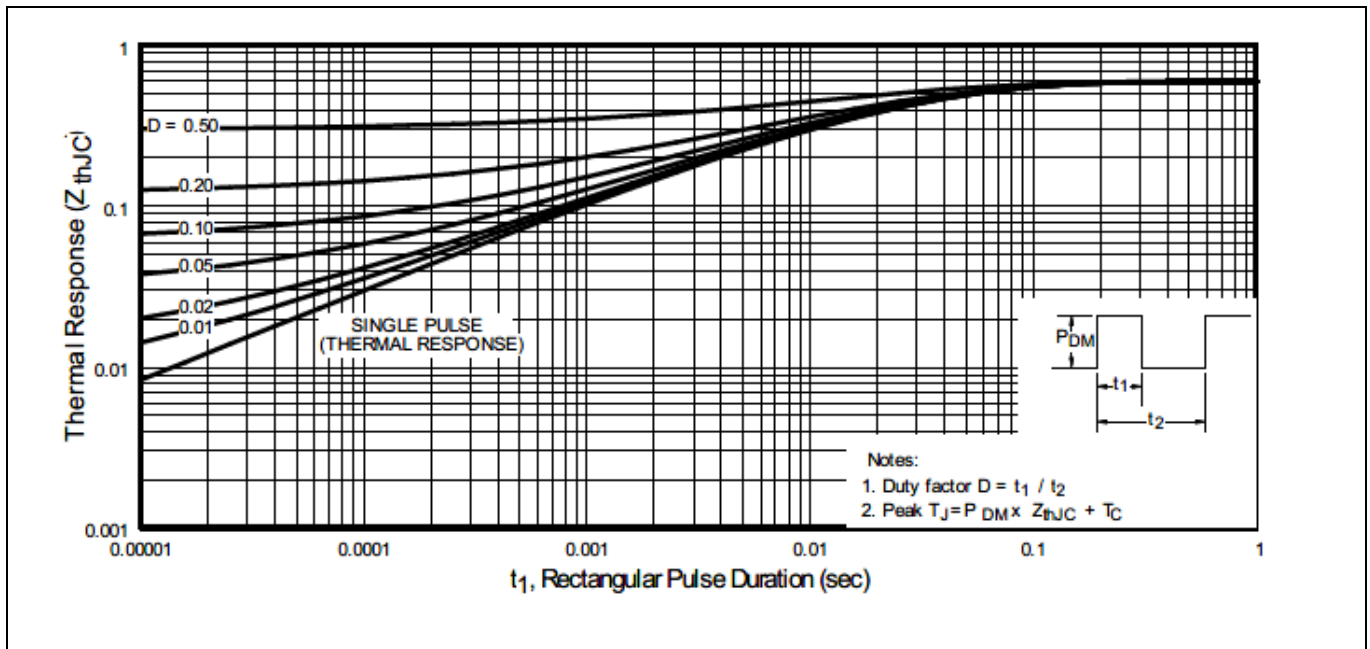
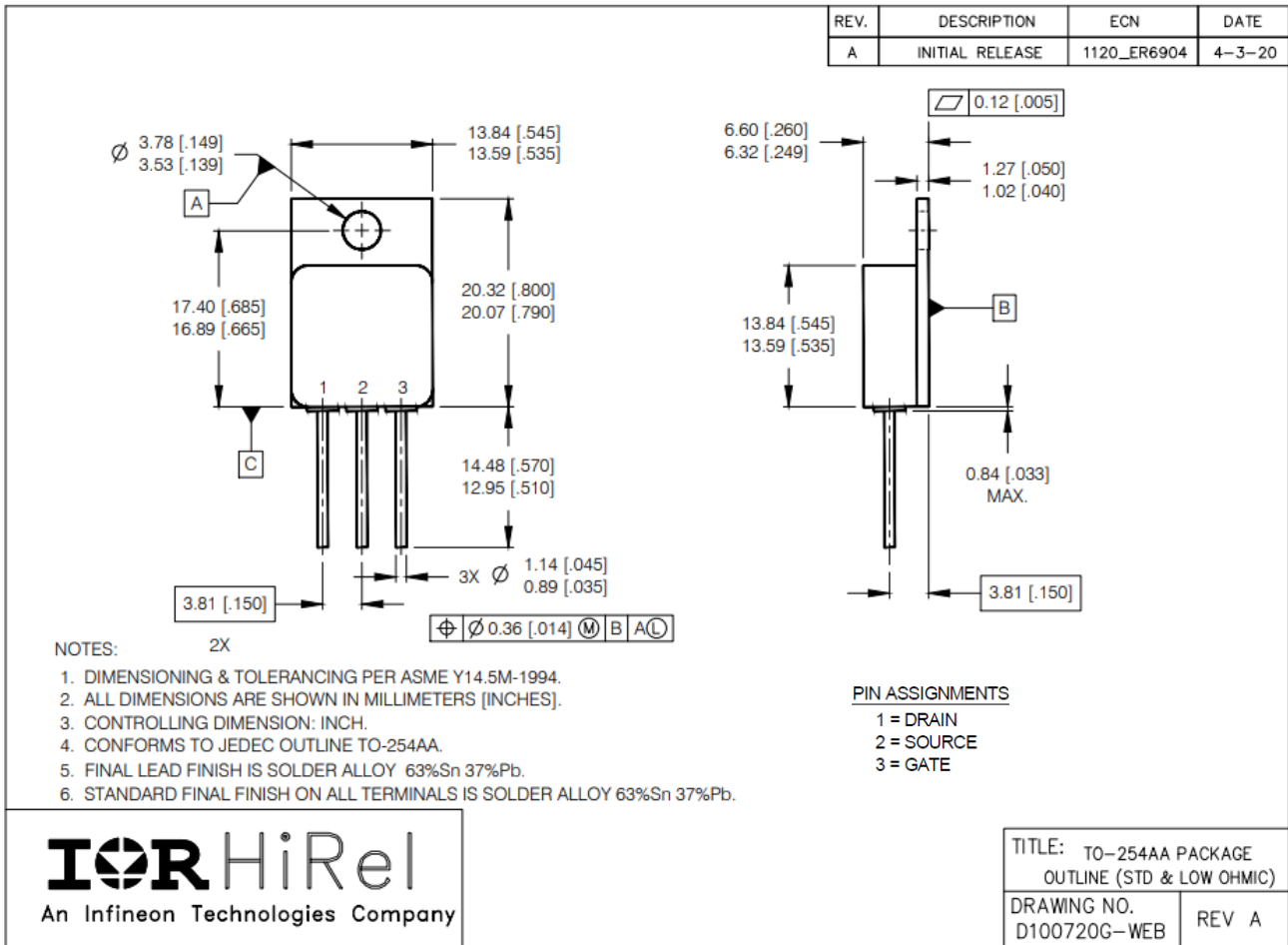


Figure 16 Maximum Effective Transient Thermal Impedance, Junction-to-Case

Package Outline

5 Package Outline

Note: For the most updated package outline, please see the website: [Low Ohmic TO-254AA](http://www.infineon.com/lowohmic)



BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

Revision history**Revision history**

Document version	Date of release	Description of changes
	7/9/2006	Final datasheet with PD number (PD-94667)
Rev A	10/7/2003	Updated Cap data & fig 10 -100KHz
Rev B	7/21/2004	Updated SEE Table and curve
Rev C	7/29/2005	Updated based on ECN-12213
Rev D	12/22/2011	Updated based on ECN-18135
Rev E	01/24/2014	Updated based on ECN-1120_02136
Rev F	04/01/2014	Updated based on ECN-1120_02315
Rev G	01/30/2017	Updated based on ECN-1120_05038
Rev H	10/30/2018	Updated based on ECN-1120_06368-2
Rev J	09/23/2022	Updated based on ECN-1120_09165

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